

學位論文系助審查流程

1. 登入論文系統 <https://cloud.ncl.edu.tw/asia/>

提醒：若系上學制（如成立碩專班）或系名有任何異動，請務必通知圖書館，以便修改系統。

◆ 圖書館網頁→電子資源→[博碩士論文系統](#)

◆ 圖書館網頁→電子資源→[博碩士論文系統](#)

◆ 圖書館網頁→電子資源→[博碩士論文系統](#)

請注意一般生帳號與在職
生帳號不同

2. 點選「研究生論文審核」進行查核

請注意若學生學籍系統是掛在其他系,但就讀是另一系時,則論文系統帳號系所務必與學籍系統一致

The screenshot shows the Asia University Thesis System homepage. On the left sidebar, under '研究生資料維護' (Graduate Student Data Maintenance), the '研究生論文審核' (Graduate Thesis Review) link is highlighted with a red box. The main content area displays a table titled '研究生帳號維護 (共 17 筆)' (Graduate Account Maintenance (17 entries)). The table lists 17 rows of account information, each with columns for 帳號 (Account Number), 密碼 (Password), 姓名 (Name), 學年度 (Academic Year), 學號 (Student ID), 寄信狀態 (Email Status), and 効用 (Action). The '寄送紀錄' (Delivery Record) column contains '寄送紀錄' (Delivery Record) for all rows. The '修改' (Modify) and '寄信' (Send Email) buttons are visible in the 'Action' column. At the bottom of the table, there are links for '目前在第 1 頁 / 共 2 頁' (Currently on page 1 / 2 pages), '下一頁 >' (Next Page), '末頁 >' (Last Page), '跳至' (Jump to), and '1 頁' (Page 1).

3. 點選”審核”

The screenshot shows the Asia University Thesis System homepage. On the left sidebar, under '研究生資料維護' (Graduate Student Data Maintenance), the '研究生論文審核' (Graduate Thesis Review) link is selected. The main content area displays a table titled '研究生論文審核' (Graduate Thesis Review). The table lists one entry with the following details: 論文中文名稱 (Chinese Name of Thesis) is '以計畫行為理論探討國小撲滿棒球', 論文英文名稱 (English Name of Thesis) is '球员从事棒球运动之行为意愿', 姓名 (Name) is '有', 狀態 (Status) is '待審中' (Pending Review), and the 効用 (Action) column contains '修改' (Modify) and '審核' (Review) buttons. The '審核' button is highlighted with a red box. At the bottom of the table, there is a link for '目前在第 1 頁 / 共 1 頁' (Currently on page 1 / 1 page).

4. 論文基本資料查核

| 基本資料 | 中外文摘要 | 目錄 | 參考文獻 | 電子全文 | 備份全文 |
|---|---|----|------|------|------|
| 論文種類： 代替論文：技術報告（應用科技類） | 1. 論文種類依實際狀況點選，點選處見下圖 | | | | |
| 研究生中文名： | 2. 紙本論文封面原「碩士論文」字樣需和系統設定的論文種類一致，分為「碩士論文」、「碩士專業實務報告」及「碩士技術報告」（如下圖）（書背也一併修改） | | | | |
| 研究生外文名： | | | | | |
| 論文中文名稱： | 研究生中文名請填與學籍系統姓名一致（尤其外籍生） | | | | |
| 論文外文名稱： | 外籍生若無中文論文名稱，請貼英文論文名稱；外文名稱字首大寫 | | | | |
| 指導教授： | | | | | |
| 中文名：王大華 外文名：WANG, DA-WA | 姓在前加逗號，名字在後，請大寫，例：王大華英文名書寫方式：WANG, DA-WA | | | | |
| 指導教授E-mail：jareelu@asia.edu.tw | | | | | |
| 口試委員： | | | | | |
| 中文名：王大華 外文名：WANG.DA-WA | 指導教授也是口試委員，請務必加 | | | | |
| 中文名：呂佳茹 外文名：LU, CHIA-JU | | | | | |
| 中文名：張祐誠 外文名：CHANG, YU-CHENG | | | | | |
| 口試日期：2020-06-02 | 審定書需與口試日期一致（自 111/6/24 起因有學系對審定書上日期有不同意見，故圖書館不複查口試日期欄位，但仍會提醒不同處，自行斟酌是否正確即可） | | | | |
| 學位類別：碩士 | | | | | |
| 院校名稱：亞洲大學 | | | | | |
| 系所名稱： | | | | | |
| 畢業學年度：108 | | | | | |
| 論文出版年：2020 | | | | | |
| 學號： | | | | | |
| 語文別：中文 | | | | | |
| 論文頁數：94 | 頁數為論文最後一頁頁碼或 PDF 檔總頁數皆可 | | | | |
| 中文關鍵詞： 灌溉用水污染 高污染潛勢判路 離子交換樹脂 土壤改善 | <p>1. 各關鍵字需分欄填寫。</p> <p>2. 外籍生若無中文關鍵字，請於中文關鍵字欄填入英文關鍵字。</p> <p>3. 中文關鍵詞不可以全部英文</p> | | | | |



5. 中英文摘要

論文審查流程.docx - Microsoft Word

臺灣博碩士論文知識加值系統管理平臺 Mozilla Firefox

ndltdcc.ndl.edu.tw/manager_thesis_listacts.php?PHPSESSID=2v4imrskne0v9qb2d26qr4u85&Pact=view&PgId=847636&dept_id=5296&examine=3#

Nanoimprint Lithography:
Si master molds are generally patterned by electron-beam lithography (EBL) that is known to be a time consuming nano patterning technique. Thus, developing mold duplication process based on high throughput technique such as nanoimprint lithography can be helpful in reducing its fabrication time and cost. The i7000E series negative e-beam resist possess a variety of characteristics desirable for NIL, such as low viscosity, low bulk-volumetric shrinkage, high Young's modulus, high thermal stability, and excellent dry-etch resistance. The excellent oxygen-etch resistance of the barrier material enables a final transfer pattern that is about three times higher than that of the original NIL mold. Based on these imprint on negative photo resist approach is used for pattern transfer into silicon substrates. The result is a high-resolution pattern with feature sizes in the range of nanometer to several microns. We combine Simprint Core simulation software for simulating nanoimprint process and to achieve uniform RLT. Our research results in low RLT as 10-20nm thicknesses for mi-I 7020E photoresist. The simulation results and experimental results are matching. A plot of how RLT across the whole stamp region changes with imprinting duration is shown using simulation. The central, thick line shows the average RLT across the entire stamp; the thin lines indicate the stamp-average RLT plus and minus one standard deviation of the cross-stamp RLT values. Simulated and calibrated for uniform residual layer thickness (RLT) and the cross-sections of RLT are plotted. In cavity filling value of 0 denotes completely empty cavities; a value of 1 in a particular location means that cavities are completely filled in that region. We have achieved completely filled cavities, i.e., value of 1 at all locations. We have achieved RLT around 10nm and even RLT at all location in pattern using mi-I 7020E photoresist imprint.

GaN GAA Nanowire:
To increase typically low output drive currents from Si Nanowire field-effect transistors (FETs), we show a GaN based GAA Nanowire FET's effectiveness. The theoretical study is focused on the three dimensional device designs, comparisons, random dopant fluctuation using IFM, and general variability issues including nanowire length, gate work function, and channel thickness are discussed. Performance of GaN GAA Nanowire is found to be increasing as Gate length is increased. Electrical characteristics of FETs including threshold voltage saturation, On/Off current ratio and sub threshold slope (SS) are analysed. GaN GAA structure let to gate control ability improvement compared to Si based Nanowire in electrical performance. The GaN GAA Nanowire subthreshold slope is $-62mV/decade$, which is close to the theoretical limit $60 mV/decade$ and leads to very high Ion/Off ratio of 1010-1011. The GaN GAA Nanowire is a very promising candidate for high-performance.

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1. 本欄只要摘要，不需貼上關鍵字。

2. 外籍生若無中文摘要，請於該欄貼上英文摘要。

6. 確認貼上目錄/圖目錄/表目錄

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2.抽驗紙本及電子檔論文頁碼是否一致且正確?
例如：第四章在第 69 頁，請查 PDF 檔的第四章頁碼是否為 69?**

7. 參考文獻查核

論文審查流程.docx - Microsoft Word

臺灣博士論文知能加值系統管理平臺 - Mozilla Firefox

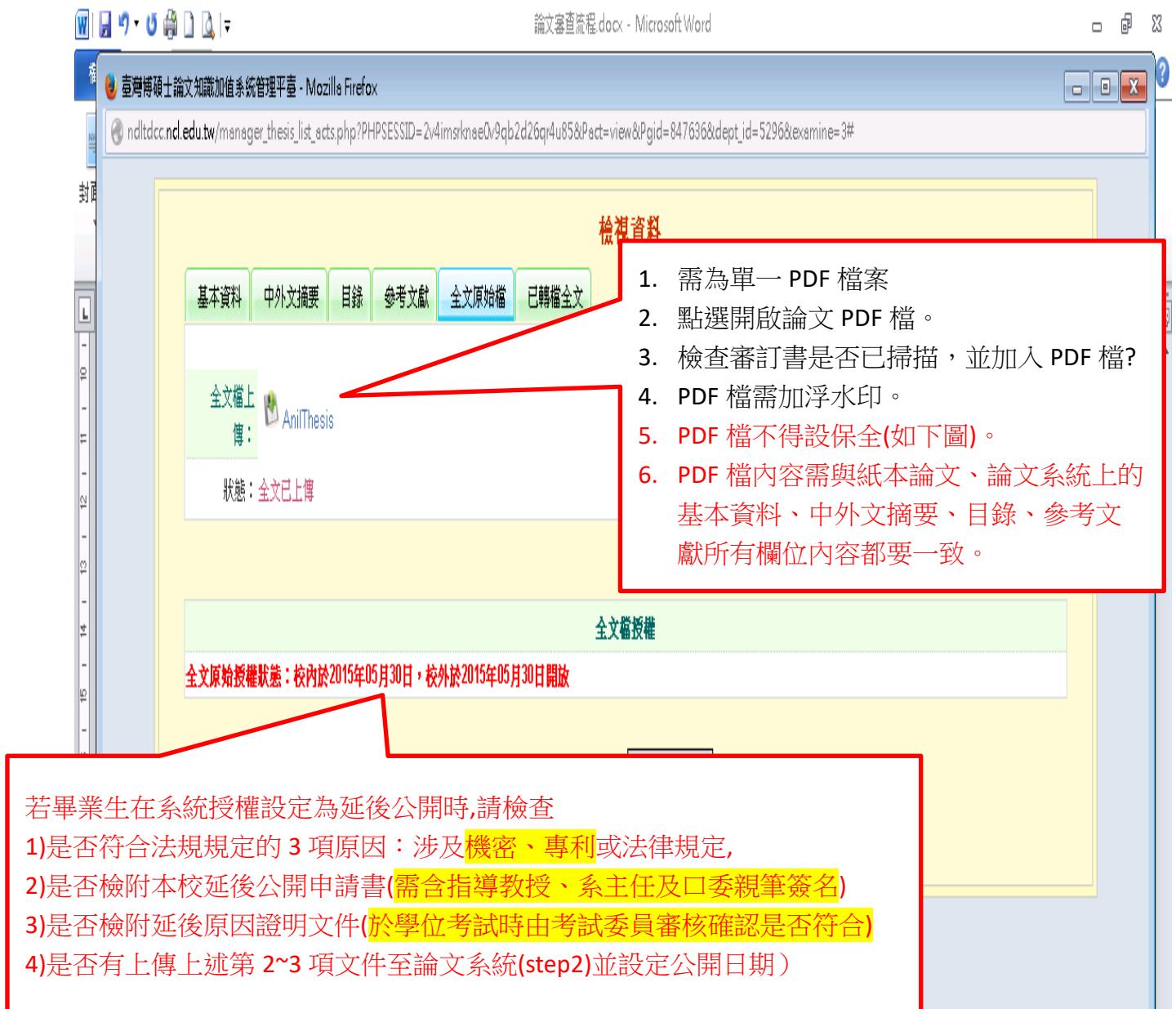
http://nidis.ncl.edu.tw/manager_thesis_list_accts.php?PHPSESSID=2e4imrsknwe0v9qz2d6q4u85&Pct=view&PgId=647636&Dept_id=5296&Examine=3#

檢視資料

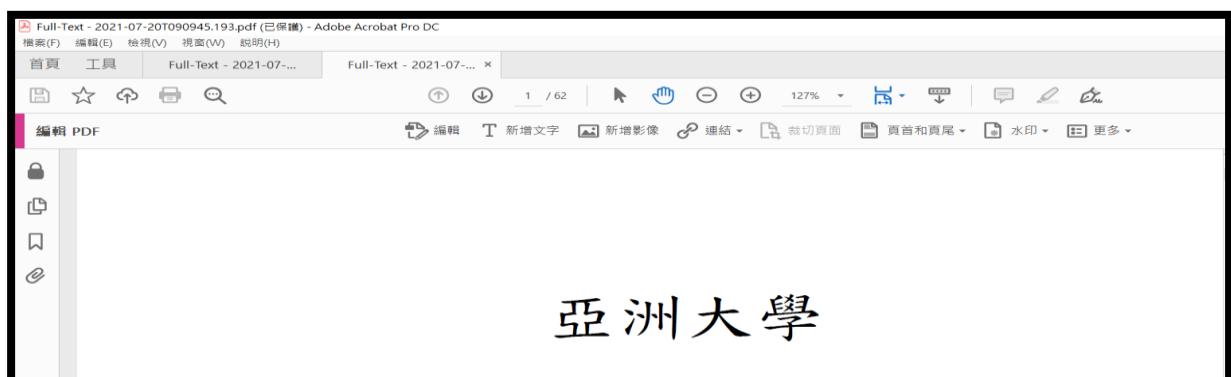
基本資料 中外文摘要 目錄 參考文獻 全文原始檔 已轉檔全文

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[19] Kang, D.J., Bae, B.-S. and Nishi, J. Fabrication of Thermally Durable sub-wavelength Periodic Structures upon Inorganic Hybrid Materials by Nanoinprint- ing. Japanese

8. 全文 PDF 檔查核



*電子全文已設保全圖示



9. 授權書查核(1張):紙本及掃描成 PDF 檔上傳系統

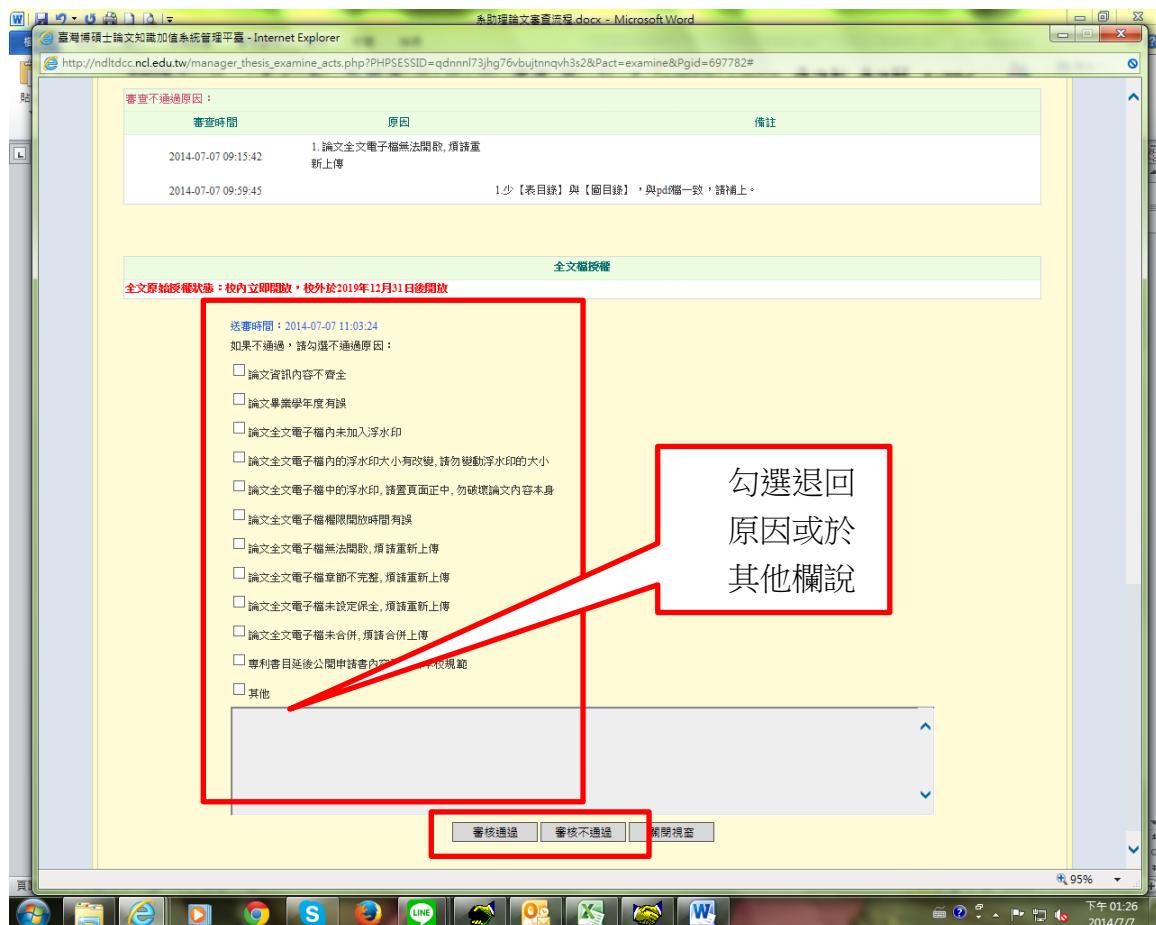
(1) 紙本授權書(1張)查核

- (2) 簽署完成之授權書完成系統上傳 PDF 檔查核:研究生基本資料下方”學位論文授權書”點選”查看”

(3) 若遇有審核退回情形,系統預設會刪除原本已上傳之授權書,研究生必需重新上傳簽署完成之授權書,系助也必需再查核 1 次是否有上傳



10. 審核結果：點選「審核通過」或「審核不通過」



- 紙本論文：檢查膠裝、封面（膠膜）、書背及封面顏色（雲彩紙，顏色有統一，圖例請至論文系統→下載區第 8 項）；紙本論文不需浮水印。
- 依國家圖書館規定**學位論文內不應含個人資訊，如電子郵件、電話、住址、身分證字號等**，應抽出或隱蔽。

13. 申請延後公開注意事項(若無可跳過)

- (1) 依「亞洲大學學位論文管理要點」第六條，延後公開原因限於涉及**機密、專利，或依法律規定**而必須延後者。
- (2) 延後年限：**至多以 5 年為限**，如有特殊需要，需逐次申請。
- (3) 申請延後公開審核程序：研究生應填具「亞洲大學學位論文延後公開申請書」(**至論文系統下載區下載最新版**)，註明延後公開原因及檢附相關證明文件，於進行學位考試前向所屬學系提出申請，並於學位口試時由口試委員審核確認是否合上述原因後簽名。
- (4) 延後公開期間：
 - 甲、每次申請電子全文及紙本論文延後公開至多以 5 年為限，如有特殊需要，需逐次申請。
 - 乙、第 2 次起之申請程序，仍應取得原所有學位考試委員審核確認，或經原就讀系所之系（所）務等會議審核確認。
- (5) 申請延後公開辦理離校論文審查時需繳交之證明文件
 - 甲、「亞洲大學學位論文延後公開申請書」1 份(經由畢業生、指導教授、學系主管及**口試委員**親筆簽名)。
 - 乙、延後原因之相關證明文件，
 - i. 涉及機密:提供相關單位開立該論文內容涉及機密之證明影本。
 - ii. 專利事項:填寫專利申請案號，提供申請專利單位回覆之影本。
 - iii. 依法不得提供:填寫原因並檢附證明文件，例如論文之研究與公司或研究機構簽訂保密合約，提供保密合約的影本。
 - 丙、**將上述文件掃描上傳至論文系統「step2 上傳全文」** → 「有申請紙本文延後公開者請點選此按鈕」→ 設定延後公開日期。
 - 丁、於到圖書館辦理論文複核時，將申請書及相關證明文件正本繳交至圖書館。
- (6) 審查時需注意
 - 甲、系統設定延後公開日期是否與上傳之申請書（請點選日期下方磁片圖示查看）一致。
 - 乙、需確認上傳之申請書各項欄位是否填寫完成、申請人/指導教授/系主任/**口試委員**需親筆簽名及系所章戳用印完成，另證明文件是否已上傳。

| 論文編號 | 論文名稱 | 姓名 | 全文檔 | 書目延後公開/專利 | 狀態 | 動作 |
|------|------|----|-----|------------|------|-----------|
| 1 | 105T | | | 2020-06-02 | 審核通過 | 檢視 |

14. 論文退件處理

當系助理已將研究生論文審核通過，但論文仍需修改時，則需向國家圖書館申請退件，申請退件步驟如下：

- (1) 在研究生帳號後點選「審核退回」

The screenshot shows the 'Graduate Student Account List' page. A red box highlights the 'Audit Return' button in the toolbar above the table. The table lists 10 accounts with columns for account number, password, name, year, grade, and audit status. The 'Audit Status' column contains buttons for 'Send Record', 'Edit', 'Email', 'Audit Return', and 'Preview'. The 'Audit Return' button is specifically highlighted.

- (2) 送出申請(通常國圖約 10-20 分鐘內處理完畢)(PS. 國圖系統人員六日不上班)

The screenshot shows the 'Audit Return Application' form. A red box highlights the 'Submit Application' button at the bottom right of the form. The form includes fields for name, email, phone, topic category, thesis ID, thesis title (in Chinese and English), and student name (in Chinese and English). To the right of the form, a smaller window shows a list of accounts with audit status buttons, similar to the one in the previous screenshot.

15. 當學期預計畢業但未畢業之研究生帳號應刪除：

- (1) 為使資訊正確，**請務必確認學生已符合畢業資格(如已修完學校規定學分)**及於研究生口試完，且論文修正完成後再核發系統帳號及密碼；
- (2) 在教務處規定的論文繳交時程結束後，請將因故無法於該學期畢業之論文系統研究生帳號刪除。

研究生帳號維護 (共 4 筆)

| 全名 | 帳號 | 密碼 | 姓名 | 學年度 | 學號 | 審核狀態 | 動作 |
|----|----|----|----|-----|----|------|-------------|
| 1 | 1 | | | | | 待審 | 刪除帳號 |
| 2 | 2 | | | | | 待審 | 刪除帳號 |
| 3 | 3 | | | | | 待審 | 刪除帳號 |

16. 其他：

- (1) 置於本校論文系統→建檔說明→論文格式規範→各系所屬之論文格式規範
Department Thesis Format List,請各系若有更新者,回傳連結給我,以便一併更新網頁.

| 系所 | 規範項目 | 檔案連結 |
|---|---------------|---|
| Department | Thesis Format | |
| 健康產業管理學系 Dept. of Healthcare Administration | 碩士班暨碩士在職專班 | http://ha.asia.edu.tw/files/11-1008-3189.php?Lang=zh-tw |
| 健康產業管理學系 Dept. of Healthcare Administration | 博士班 | http://ha.asia.edu.tw/files/11-1008-1658.php?Lang=zh-tw |
| 食品營養與保健生技學系 Dept. of Food Nutrition and Health Biotechnology | 無規範 | 無規範 |